
2SB1032(K)

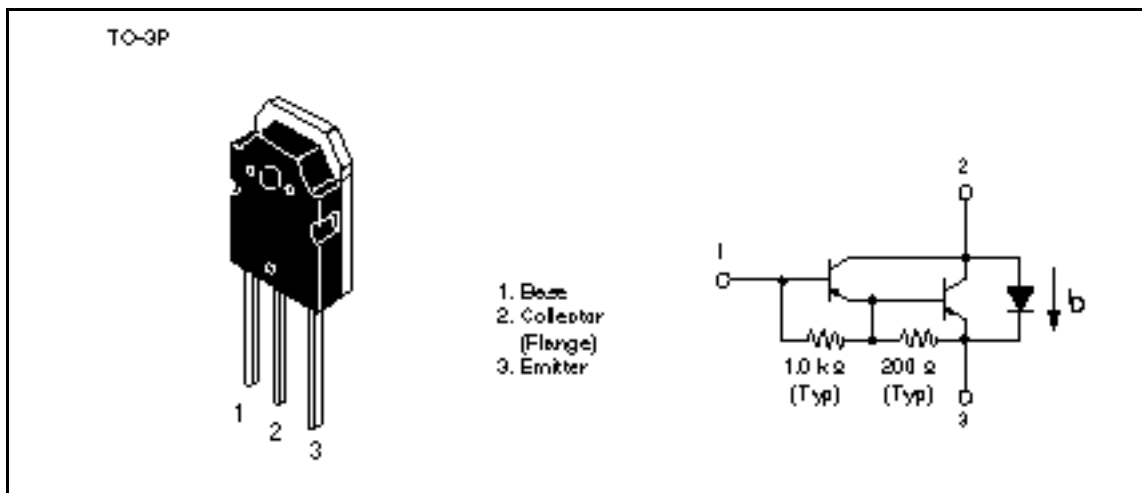
Silicon PNP Triple Diffused

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Application

Power switching complementary pair with 2SD1436(K)

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V_{CEO}	-120	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I_C	-10	A
Collector peak current	$I_{C(peak)}$	-15	A
C to E diode forward current	I_D^{*1}	10	A
Collector power dissipation	P_C^{*1}	80	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

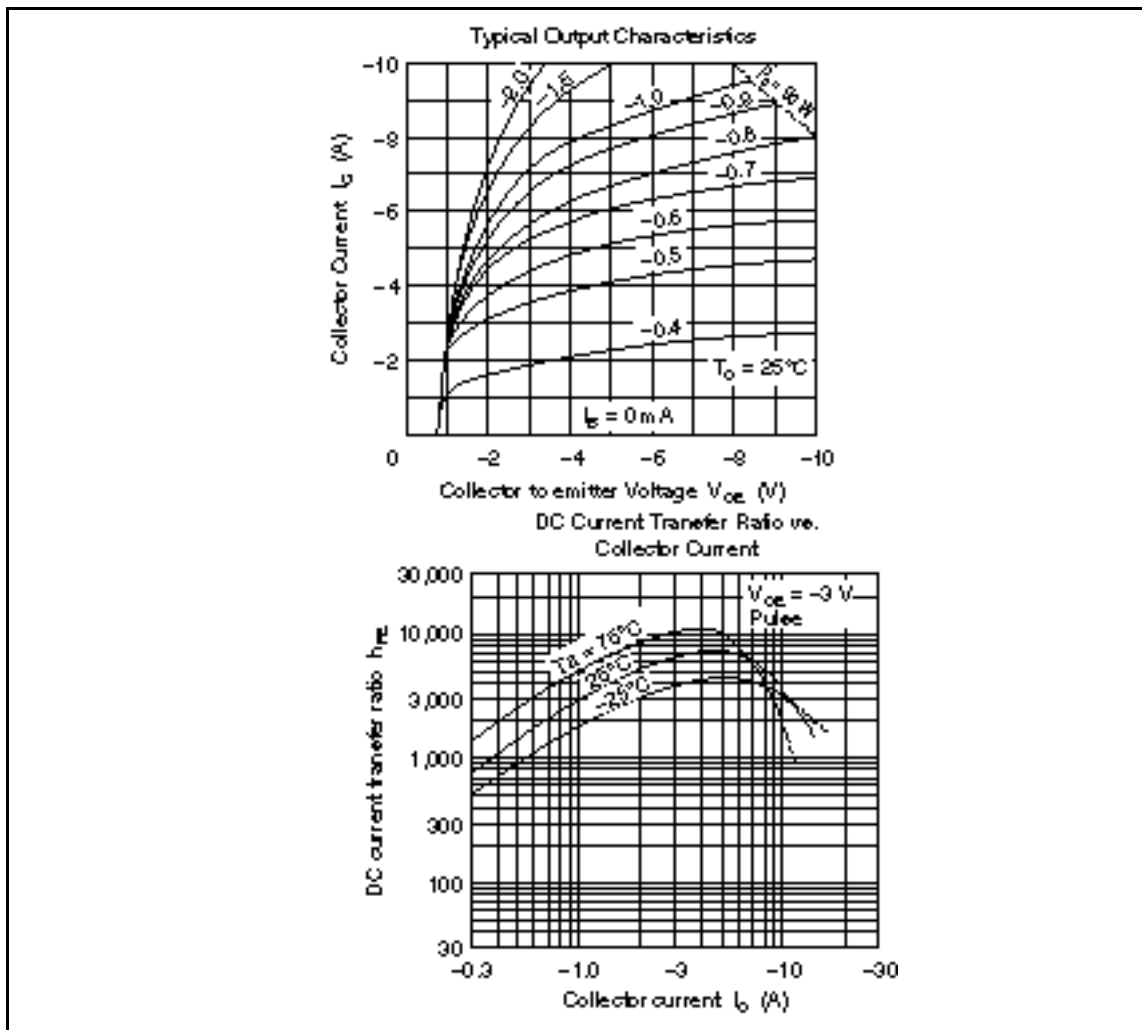
Note: 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

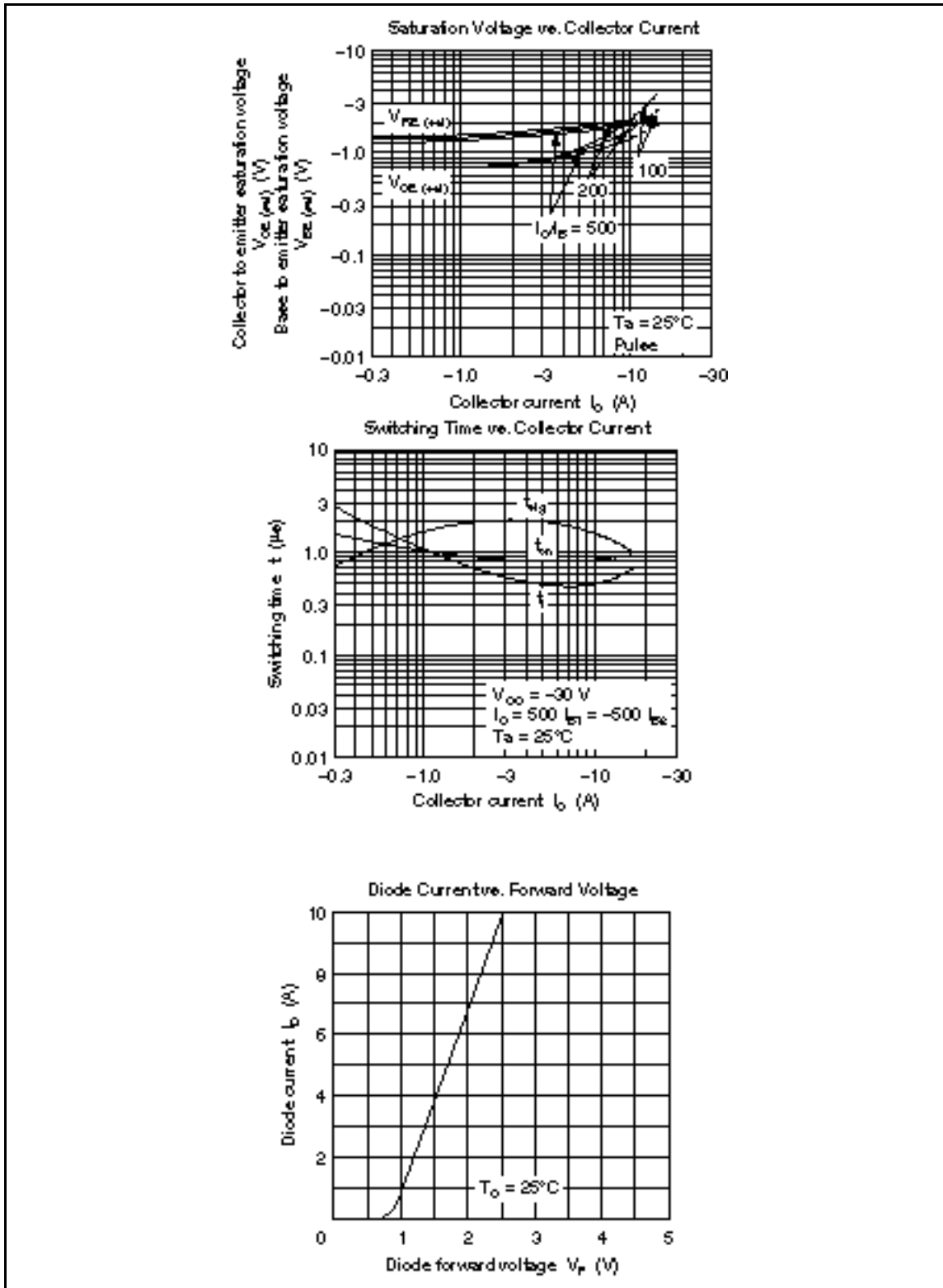
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	—	—	V	$I_C = -25\text{ mA}$, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7	—	—	V	$I_E = -200\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-100	μA	$V_{CB} = -120\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	-10	μA	$V_{CE} = -100\text{ V}$, $R_{BE} =$
DC current transfer ratio	h_{FE}	1000	—	20000		$V_{CE} = -3\text{ V}$, $I_C = -5\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	-1.5	V	$I_C = -5\text{ A}$, $I_B = -10\text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	-3.0	V	$I_C = -10\text{ A}$, $I_B = -0.1\text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	-2.0	V	$I_C = -5\text{ A}$, $I_B = -10\text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	-3.5	V	$I_C = -10\text{ A}$, $I_B = -0.1\text{ A}^{*1}$
C to E diode forward voltage	V_D	—	—	3.0	V	$I_D = 10\text{ A}^{*1}$
Turn on time	t_{on}	—	0.8	—	μs	$V_{CC} = -30\text{ V}$,
Turn off time	t_{off}	—	4.0	—	μs	$I_C = -5\text{ A}$, $I_{B1} = -I_{B2} = -10\text{ mA}$

Note: 1. Pulse test

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